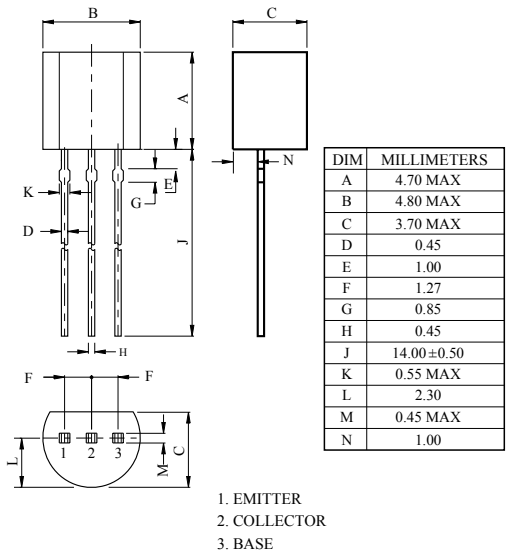
HIGH CURRENT APPLICATION.

FEATURE

· Complementary to KTC3211.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. EMITTER
2. COLLECTOR
3. BASE

TO-92

MAXIMUM RATING (Ta=25℃)

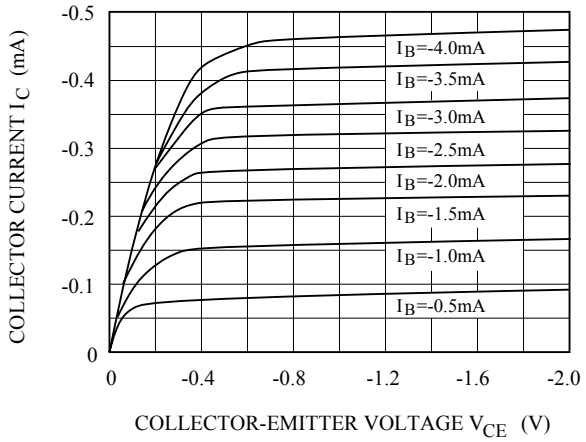
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-1.5	A
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

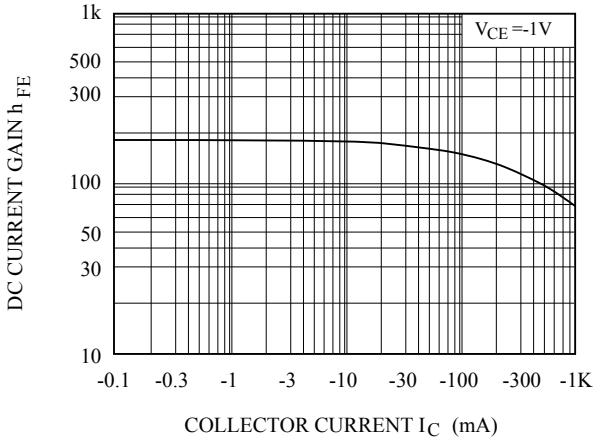
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-35V, I_E=0	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-6V, I_C=0	-	-	-100	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-2mA, I_B=0	-25	-	-	V
DC Current Gain	h_{FE}(1)	V_{CE}=-1V, I_C=-5mA	45	170	-	
	h_{FE}(2) (Note)	V_{CE}=-1V, I_C=-100mA	85	160	300	
	h_{FE}(3)	V_{CE}=-1V, I_C=-800mA	40	80	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-800mA, I_B=-80mA	-	-0.28	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-800mA, I_B=-80mA	-	-0.98	-1.2	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1V, I_C=-10mA	-	-0.66	-1.0	V
Transition Frequency	f_T	V_{CE}=-10V, I_C=-50mA	100	200	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, f=1MHz, I_E=0	-	15	-	pF

Note : h_{FE}(2) Classification O:85～160 , Y:120～200 , GR:160～300

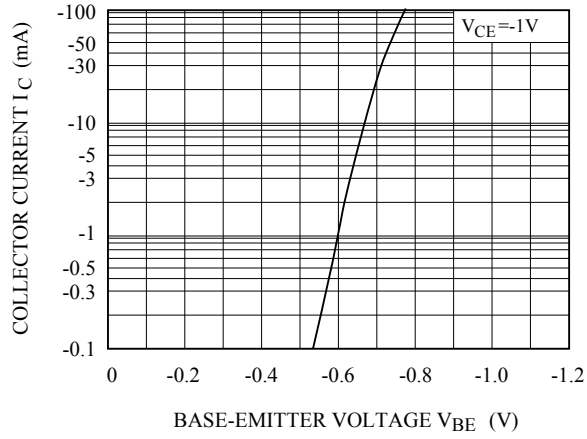
I_C - V_{CE}



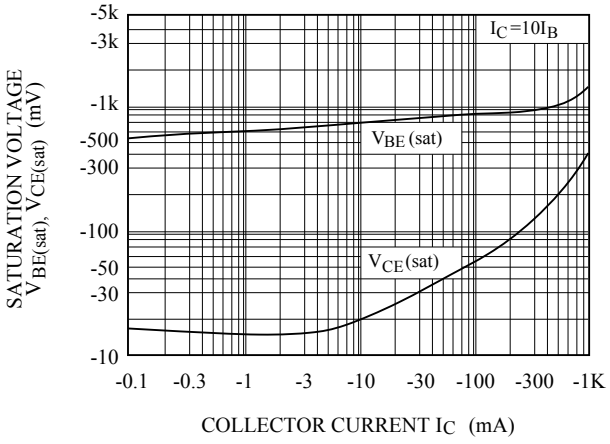
h_{FE} - I_C



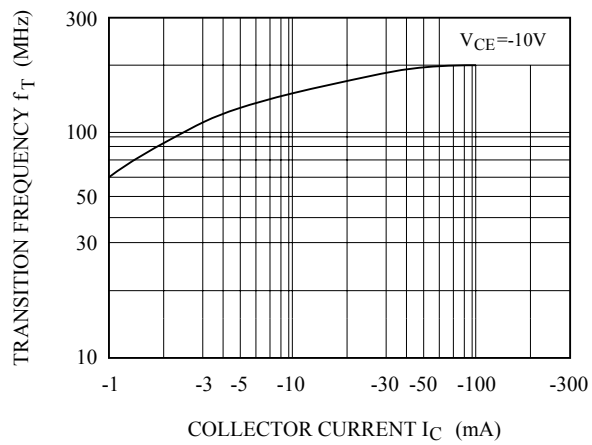
I_C - V_{BE}



$V_{BE(sat)}$, $V_{CE(sat)}$ - I_C



f_T - I_C



C_{ob} - V_{CB}

